

Docket No. 246244US2SRD/phh



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF: Masato KOYAMA, et al.

SERIAL NO: 10/726,606

GAU:

FILED: December 4, 2003

EXAMINER:

FOR: SEMICONDUCTOR DEVICE AND METHOD OF MANUFACTURING SEMICONDUCTOR DEVICE

INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR 1.97

COMMISSIONER FOR PATENTS
ALEXANDRIA, VIRGINIA 22313

SIR:

Applicant(s) wish to disclose the following information.

REFERENCES

- ☒ The applicant(s) wish to make of record the references listed on the attached form PTO-1449. Copies of the listed references are attached, where required, as are either statements of relevancy or any readily available English translations of pertinent portions of any non-English language references.
- ☐ A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

RELATED CASES

- ☐ Attached is a list of applicant's pending application(s) or issued patent(s) which may be related to the present application. A copy of the patent(s), together with a copy of the claims and drawings of the pending application(s) is attached along with PTO 1449.
- ☐ A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

CERTIFICATION

- ☐ Each item of information contained in this information disclosure statement was first cited in any communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this statement.
- ☐ No item of information contained in this information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to the knowledge of the undersigned, having made reasonable inquiry, was known to any individual designated in 37 CFR §1.56(c) more than three months prior to the filing of this statement.

DEPOSIT ACCOUNT

- ☒ Please charge any additional fees for the papers being filed herewith and for which no check or credit card payment is enclosed herewith, or credit any overpayment to deposit account number 15-0030. A duplicate copy of this sheet is enclosed.

Respectfully submitted,

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SHEET 1 OF 1

Form PTO 1449
(Modified)

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICE

ATTY DOCKET NO.

246244US2SRD

SERIAL NO.

10/726,606

LIST OF REFERENCES CITED BY APPLICANT

APPLICANT

Masato KOYAMA, et al.

FILING DATE

December 4, 2003

GROUP

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	AA	6,613,658	09/02/2003	M. KOYAMA, et al.			
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						
	AL						
	AM						
	AN						

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION	
					YES	NO
	AO					
	AP					
	AQ					
	AR					
	AS					
	AT					
	AU					
	AV					

OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)

✓	AW	C. S. KANG, et al., Applied Physics Letters, vol. 81, no. 14, pages 2593-2595, "BONDING STATES AND ELECTRICAL PROPERTIES OF ULTRATHIN HfOxNy GATE DIELECTRICS", September 30, 2002				
✓	AX	M. R. VISOKAY, et al., Applied Physics Letters, vol. 80, no. 17, pages 3183-3185, "APPLICATION OF HfSiON AS A GATE DIELECTRIC MATERIAL", April 29, 2002				
✓	AY	A. KANEKO, et al., Extended Abstracts of the 2002 International Conference on Solid State Devices and Materials, pages 742-743, "PLASMA NITRIDATION TECHNIQUE FOR THE FORMATION OF THERMALLY STABLE Hf-SILICATE GATE DIELECTRIC WITH CONTROLLED NITROGEN PROFILE", 2002				
	AZ				<input type="checkbox"/> Additional References sheet(s) attached	

Examiner

Date Considered

*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.